

E Series Power MOSFET

| PRODUCT SUMMARY | | |
|---|-----------------|-------|
| V_{DS} (V) at T_J max. | 550 | |
| $R_{DS(on)}$ max. at 25 °C (Ω) | $V_{GS} = 10$ V | 0.184 |
| Q_g max. (nC) | 92 | |
| Q_{gs} (nC) | 10 | |
| Q_{gd} (nC) | 19 | |
| Configuration | Single | |

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

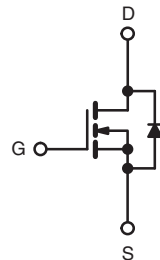
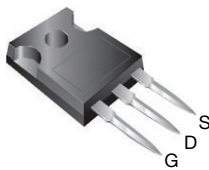


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Computing
 - PC silver box / ATX power supplies
- Lighting
 - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
 - Power factor correction (PFC)
 - Two switch forward converter
 - Flyback converter
- Switch mode power supplies (SMPS)

TO-247AC



N-Channel MOSFET


| ORDERING INFORMATION | |
|---------------------------------|----------------|
| Package | TO-247AC |
| Lead (Pb)-free and Halogen-free | SiHG20N50E-GE3 |

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | |
|---|---------------------------------|----------------|------|
| PARAMETER | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | V_{DS} | 500 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Gate-Source Voltage AC ($f > 1$ Hz) | | 30 | |
| Continuous Drain Current ($T_J = 150$ °C) | V_{GS} at 10 V | $T_C = 25$ °C | A |
| | | $T_C = 100$ °C | |
| Pulsed Drain Current ^a | I_{DM} | 42 | |
| Linear Derating Factor | | 1.4 | W/°C |
| Single Pulse Avalanche Energy ^b | E_{AS} | 204 | mJ |
| Maximum Power Dissipation | P_D | 179 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | °C |
| Drain-Source Voltage Slope | $V_{DS} = 0$ V to 80 % V_{DS} | 70 | V/ns |
| Reverse Diode dV/dt ^d | | 32 | |
| Soldering Recommendations (Peak Temperature) ^c | for 10 s | 300 | °C |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 3.8$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 0.7 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|---------------------|---|------|-------|-----------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 500 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | - | 0.59 | - | V/ $^\circ\text{C}$ |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$ | - | - | 1 | μA |
| | | $V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ | - | - | 10 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$ | - | 0.160 | 0.184 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 30\text{ V}$, $I_D = 10\text{ A}$ | - | 4.4 | - | S |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$ | - | 1640 | - | μF |
| Output Capacitance | C_{oss} | | - | 87 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 6 | - | |
| Effective Output Capacitance, Energy Related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 400\text{ V}$, $V_{GS} = 0\text{ V}$ | - | 73 | - | μF |
| Effective Output Capacitance, Time Related ^b | $C_{o(tr)}$ | | - | 222 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$, $V_{DS} = 400\text{ V}$ | - | 46 | 92 | nC |
| Gate-Source Charge | Q_{gs} | | - | 10 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 19 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 400\text{ V}$, $I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$ | - | 17 | 34 | ns |
| Rise Time | t_r | | - | 27 | 54 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 48 | 96 | |
| Fall Time | t_f | | - | 25 | 50 | |
| Gate Input Resistance | R_g | $f = 1\text{ MHz}$, open drain | - | 0.83 | - | Ω |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p-n junction diode  | - | - | 19 | A |
| Pulsed Diode Forward Current | I_{SM} | | - | - | 42 | |
| Diode Forward Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}$, $I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$ | - | - | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}$, $I_F = I_S = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 25\text{ V}$ | - | 293 | - | ns |
| Reverse Recovery Charge | Q_{rr} | | - | 4.0 | - | μC |
| Reverse Recovery Current | I_{RRM} | | - | 26 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

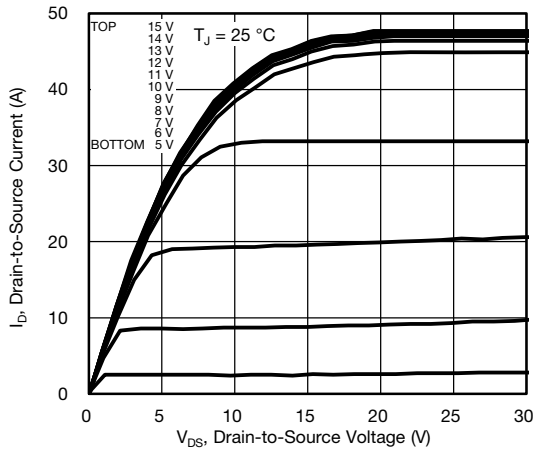


Fig. 1 - Typical Output Characteristics

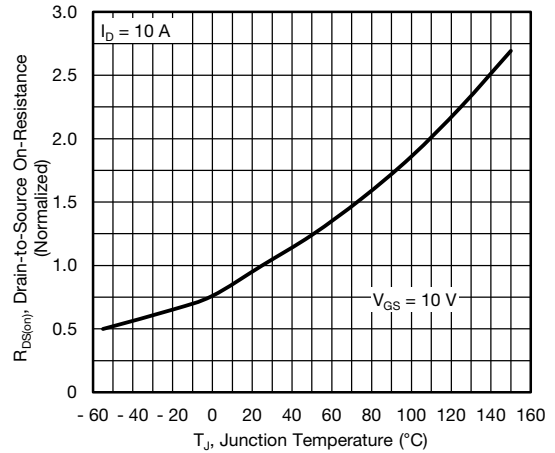


Fig. 4 - Normalized On-Resistance vs. Temperature

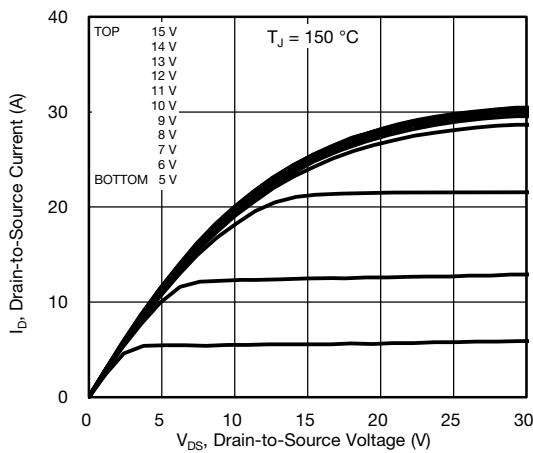


Fig. 2 - Typical Output Characteristics

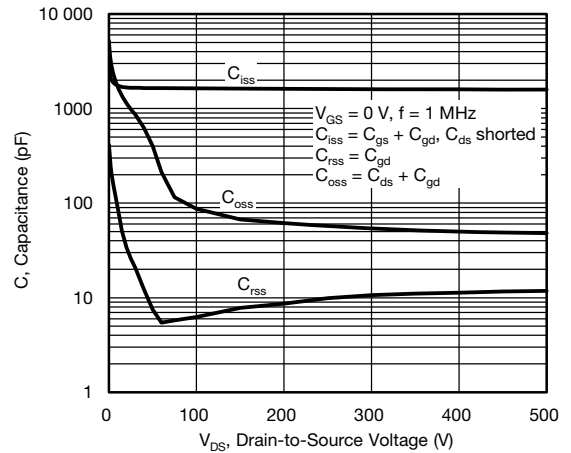


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

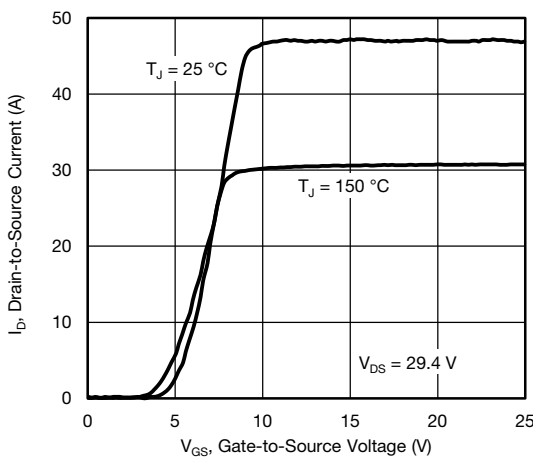


Fig. 3 - Typical Transfer Characteristics

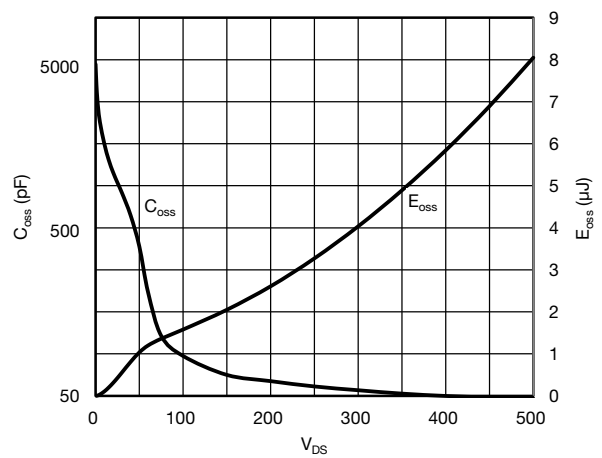


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

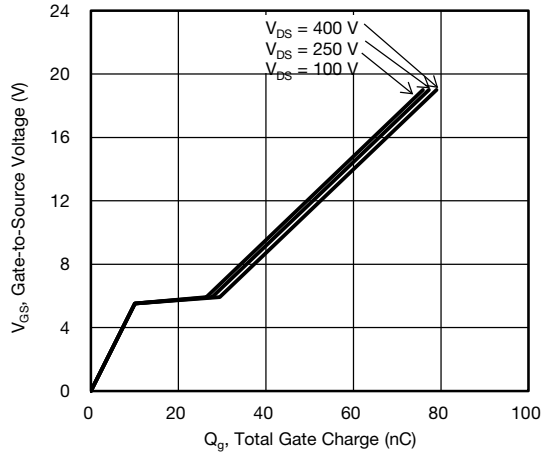


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

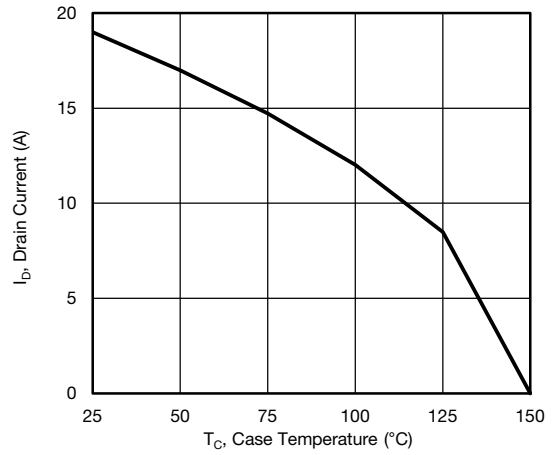


Fig. 10 - Maximum Drain Current vs. Case Temperature

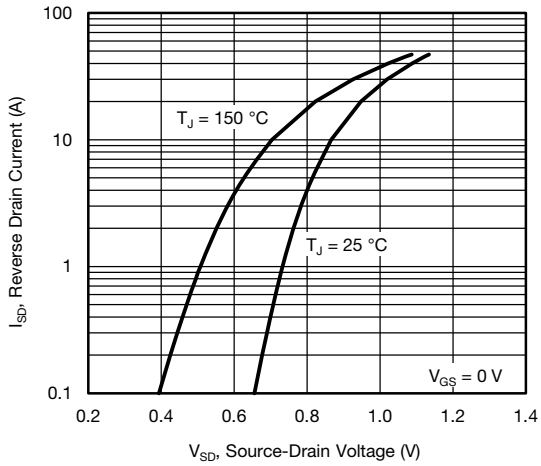


Fig. 8 - Typical Source-Drain Diode Forward Voltage

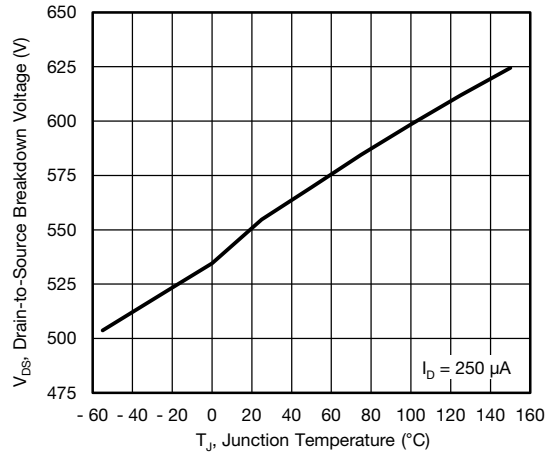


Fig. 11 - Temperature vs. Drain-to-Source Voltage

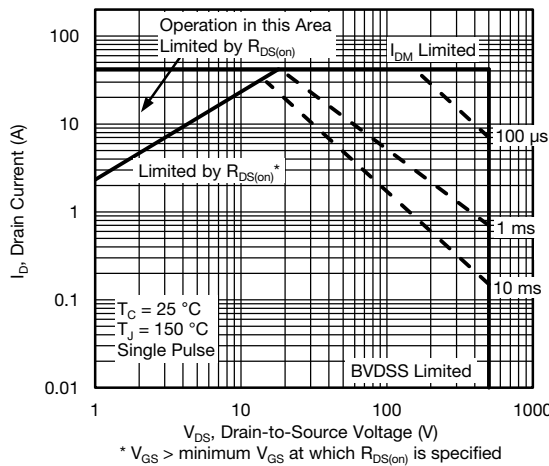


Fig. 9 - Maximum Safe Operating Area

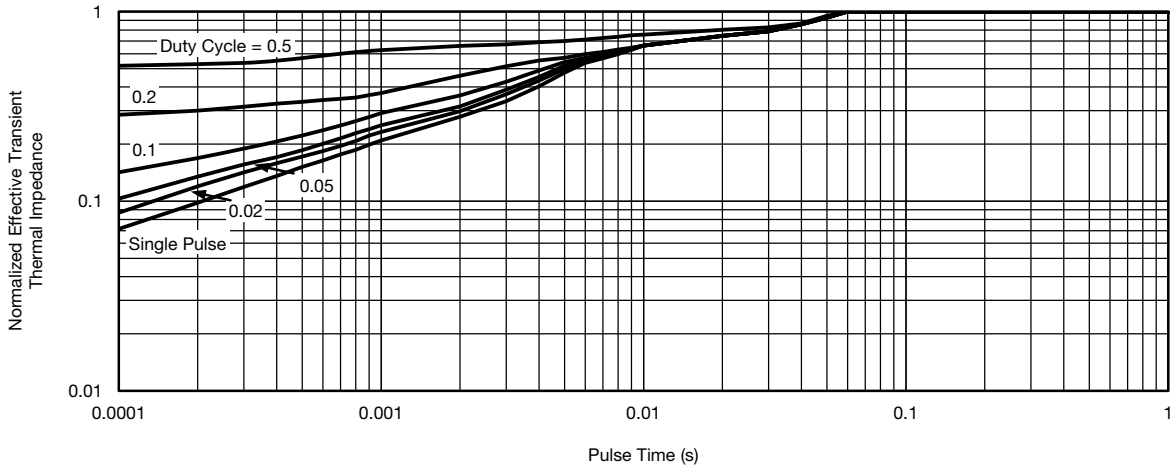


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

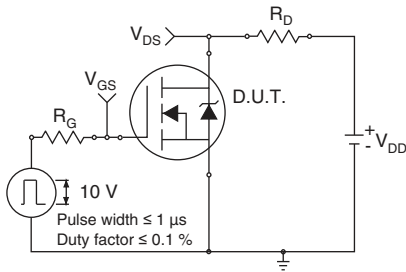


Fig. 13 - Switching Time Test Circuit

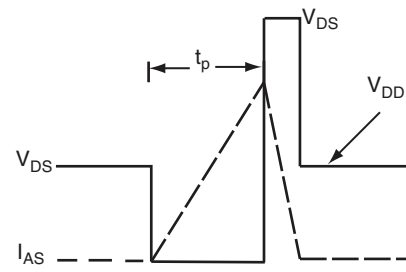


Fig. 16 - Unclamped Inductive Waveforms

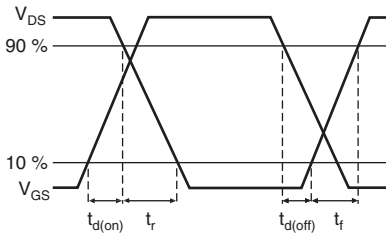


Fig. 14 - Switching Time Waveforms

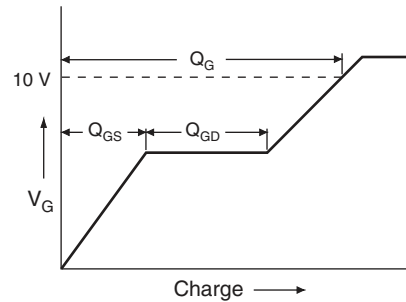


Fig. 17 - Basic Gate Charge Waveform

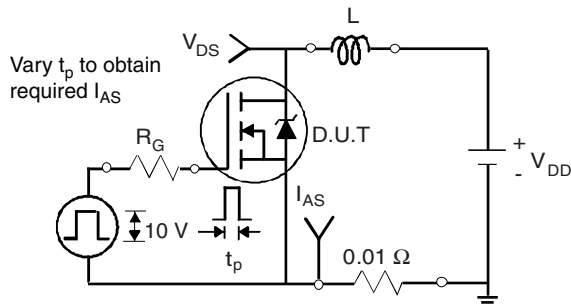


Fig. 15 - Unclamped Inductive Test Circuit

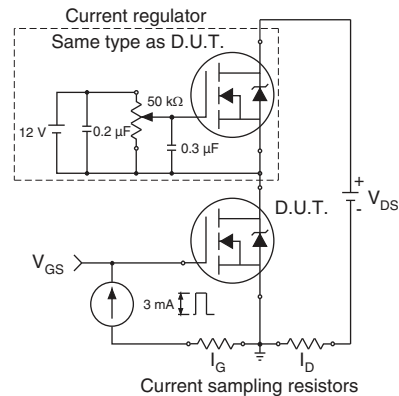


Fig. 18 - Gate Charge Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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